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AMENDMENTS TO THE CLAIMS**Claims 1-24 (cancelled)**

Claim 25 (previously presented): A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect, provided
on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-
th mask;
an (n+1)-th patterned mask containing a material having a growth suppressing material
substantially provided above an opening of the n-th patterned mask; and an (n+1)-th nitride
semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask,
wherein the n-th patterned mask and the (n+1)-th patterned mask are respectively patterned
in a stripe shape, and a direction of the stripe of the n-th patterned mask is twisted from a direction
of the stripe of the (n+1)-th patterned mask.

Claim 26 (original): A light-emitting device produced by using the semiconductor substrate
of claim 25.

Claim 27 (previously presented): A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect, provided
on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-
th mask;
an (n+1)-th patterned mask containing a material having a growth suppressing effect,
provided so as to be at an angle of about 90° or 120° relative to the n-th patterned mask; and an

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(n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask.

Claim 28 (previously presented): A light emitting device produced by using the semiconductor substrate of claim 37.

Claims 29-36 (cancelled)

Claim 37 (previously presented): A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect, provided on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-th mask;
an (n+1)-th patterned mask containing a material having a growth suppressing material substantially provided above an opening of the n-th patterned mask; and an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask,
wherein the first to (n+1)-th patterned masks are patterned in such a manner that a combination of the first to (n+1)-th patterned masks covers the entire surface of the lower substrate.

Claim 38 (previously presented): A light emitting device produced by using the semiconductor substrate of claim 37.

Claim 39 (previously presented): A semiconductor substrate according to claim 25, wherein a width of the stripe of the (n+1)-th patterned mask is equal to or larger than a width of the stripe of the n-th patterned mask.

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Claim 40 (previously presented): A semiconductor substrate according to claim 27, wherein a width of the stripe of the (n+1)-th patterned mask is equal to or larger than a width of the stripe of the n-th patterned mask.

Claim 41 (previously presented): A semiconductor substrate according to claim 37, wherein a width of the stripe of the (n+1)-th patterned mask is equal to or larger than a width of the stripe of the n-th patterned mask.

Claim 42 (previously presented): A semiconductor substrate according to claim 25, wherein the n-th nitride semiconductor crystal layer is made of AlGaN or InGaN.

Claim 43 (previously presented): A semiconductor substrate according to claim 27, wherein the n-th nitride semiconductor crystal layer is made of AlGaN or InGaN.

Claim 44 (previously presented): A semiconductor substrate according to claim 37, wherein the n-th nitride semiconductor crystal layer is made of AlGaN or InGaN.

Claim 45 (previously presented): A semiconductor substrate according to claim 25, wherein a stripe width of the second mask is smaller than each opening of the first mask.

Claim 46 (previously presented): A semiconductor substrate according to claim 27, wherein a stripe width of the second mask is smaller than each opening of the first mask.

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Claim 47 (previously presented): A semiconductor substrate according to claim 37, wherein a stripe width of the second mask is smaller than each opening of the first mask.

Claim 48 (previously presented): A semiconductor substrate according to claim 25, wherein the n-th and (n+1)-th patterned masks are formed of the same material.

Claim 49 (previously presented): A semiconductor substrate according to claim 27, wherein the n-th and (n+1)-th patterned masks are formed of the same material.

Claim 50 (previously presented): A semiconductor substrate according to claim 37, wherein the n-th and (n+1)-th patterned masks are formed of the same material.

Claim 51 (previously presented): A semiconductor substrate according to claim 25, wherein the thickness of the n-th and (n+1)-th masks are the same as each other.

Claim 52 (previously presented): A semiconductor substrate according to claim 27, wherein the thickness of the n-th and (n+1)-th masks are the same as each other.

Claim 53 (previously presented): A semiconductor substrate according to claim 37, wherein the thickness of the n-th and (n+1)-th masks are the same as each other.

Claim 54 (previously presented): A semiconductor substrate according to claim 25, wherein the lower substrate is GaN.

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Claim 55 (previously presented): A semiconductor substrate according to claim 27, wherein the lower substrate is GaN.

Claim 56 (previously presented): A semiconductor substrate according to claim 37, wherein the lower substrate is GaN.

Claim 57 (cancelled)

Claim 58 (previously presented): A semiconductor substrate comprising:

an n-th patterned mask containing a material having a growth suppressing effect, provided on or above a lower substrate, wherein n is an integer of 1 or more;

an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-th mask;

an (n+1)-th patterned mask containing a material having a growth suppressing effect, provided so as to be at an angle of about 90° or more relative to the n-th patterned mask; and

an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask.

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